TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE (DARLINGTON POWER)

2 S D 1 4 0 9 A

IGNITER APPLICATIONS

HIGH VOLTAGE SWITCHING APPLICATIONS

• High DC Current Gain : $h_{FE} = 600$ (Min.) $(V_{CE} = 2 \text{ V}, I_{C} = 2 \text{ A})$

• Monolithic Construction with Built-In Base-Emitter Shunt Resistor.

MAXIMUM RATINGS (Tc = 25°C)

| CHARACTERISTIC | | SYMBOL | RATING | UNIT | |
|---------------------------|--------------------|--------------------|---------|----------------------|--|
| Collector-Base Voltage | | v_{CBO} | 600 | V | |
| Collector-Emitter Voltage | | v_{CEO} | 400 | V | |
| Emitter-Base Voltage | | $v_{ m EBO}$ | 5 | V | |
| Collector Current | | $I_{\mathbf{C}}$ | 6 | A | |
| Base Current | | $I_{\mathbf{B}}$ | 1 | A | |
| Collector Power | $Ta = 25^{\circ}C$ | Da | 2.0 | w | |
| Dissipation | $Tc = 25^{\circ}C$ | $_{\mathrm{PC}}$ | 25 |] ** | |
| Junction Temperature | | T_{j} | 150 | $^{\circ}\mathrm{C}$ | |
| Storage Temperature Range | | $\mathrm{T_{stg}}$ | -55~150 | $^{\circ}\mathrm{C}$ | |

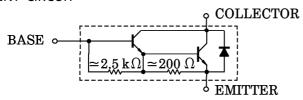
INDUSTRIAL APPLICATIONS

Weight: 1.7 g (Typ.)

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TOSHIBA

EQUIVALENT CIRCUIT

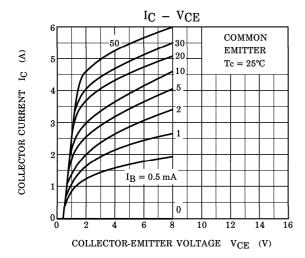


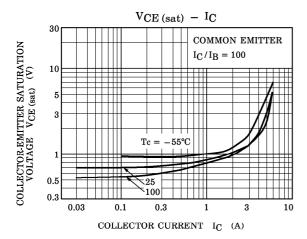
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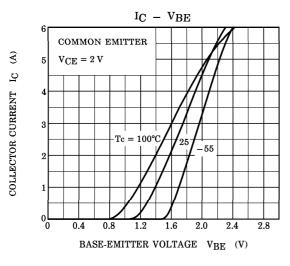
ELECTRICAL CHARACTERISTICS (Tc = 25°C)

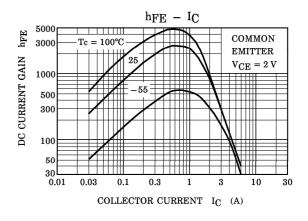
| CHARA | CTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|----------------------------|-----------------|--------------------------|---|------|------|------|------|
| Collector Cut- | off Current | I_{CBO} | $V_{CB} = 600 \text{ V}, I_{E} = 0$ | _ | _ | 0.5 | mA |
| Emitter Cut-o | off Current | I_{EBO} | $V_{EB} = 5 \text{ V}, I_{C} = 0$ | _ | _ | 3 | mA |
| Collector-Emi Voltage | tter Breakdown | V (BR) CEO | $I_{\mathrm{C}}=10\mathrm{mA},~I_{\mathrm{B}}=0$ | 400 | _ | _ | V |
| DC Current Gain | | h _{FE} (1) | $V_{CE} = 2 V, I_{C} = 2 A$ | 600 | _ | | |
| | | h _{FE} (2) | $V_{ m CE}=2 m V,~I_{ m C}=4 m A$ | 100 | _ | | |
| Collector-Emi Voltage | tter Saturation | V _{CE} (sat) | $I_{\rm C} = 4~{ m A},~I_{ m B} = 0.04~{ m A}$ | _ | _ | 2.0 | V |
| Base-Emitter Voltage | Saturation | V _{BE} (sat) | $I_{\rm C} = 4~{ m A},~I_{ m B} = 0.04~{ m A}$ | _ | _ | 2.5 | V |
| Emitter-Collection Voltage | ctor Forward | v_{ECF} | $I_E = 4 A, I_B = 0$ | _ | _ | 3.0 | V |
| Collector Out | put Capacitance | C_{ob} | $V_{CB} = 50 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$ | _ | 35 | _ | pF |
| Switching Time | Turn-on Time | t _{on} | OUTPUT IN- 20 μs PUT I _{B1} | _ | 1 | _ | |
| | Storage Time | $\mathbf{t}_{	ext{stg}}$ | I_{B1} I_{B2} I_{B2} | | 8 | _ | μs |
| | Fall Time | t_f | $I_{B1} = -I_{B2} = 0.04 \text{ A}, V_{CC}$ $DUTY \ CYCLE \le 1\% = 100 \text{ V}$ | _ | 5 | _ | |

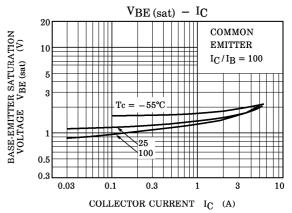
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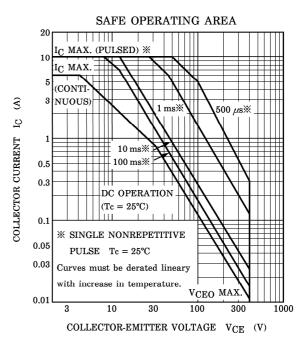




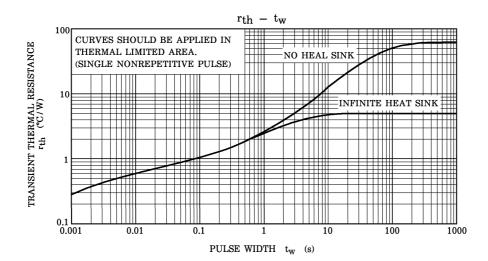








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